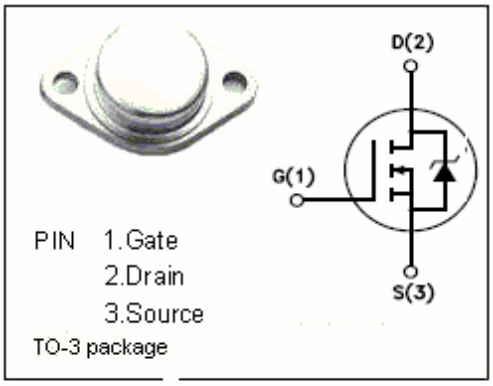
isc N-Channel MOSFET Transistor IRF351

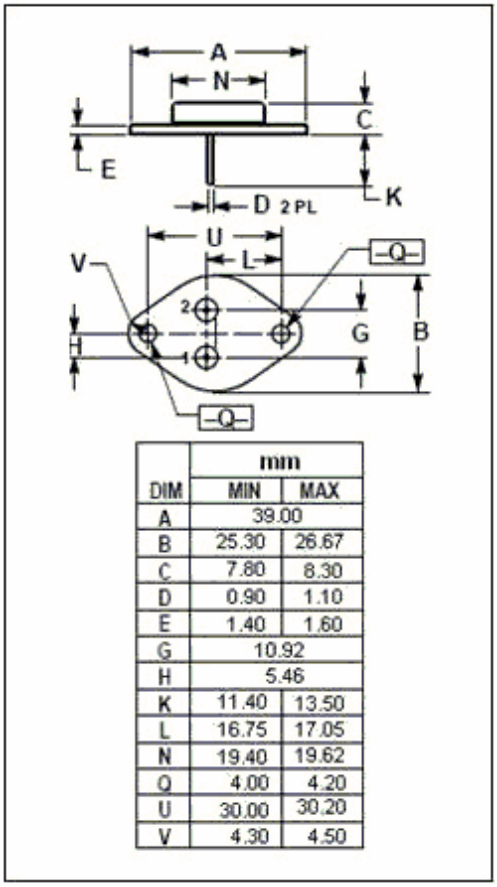
DESCRIPTION

- V_{GS} Rated at ±20V
- Silicon Gate for Fast Switching Speeds
- I_{DSS},$V_{DS(on)}$,SOA and $V_{GS(th)}$ specified at Elevated temperature
- Rugged



APPLICATIONS

- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	350	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	15	A
P_{tot}	Total Dissipation@TC=25℃	150	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.83	℃/W
$R_{th\ j\text{-}A}$	Thermal Resistance,Junction to Ambient	30	℃/W

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• ELECTRICAL CHARACTERISTICS (T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 0.25mA	350			V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 0.25mA	2		4	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 10V; I_D= 8.0A			0.3	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V; V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 350V; V_{GS}= 0			250	uA
V_{SD}	Diode Forward Voltage	I_F= 15A; V_{GS}= 0			1.6	V
Ciss	Input Capacitance	V_{DS}=25V,V_{GS}=0V, F=1.0MHz		2000	3000	pF
Coss	Output Capacitance			400	600	pF
Crss	Reverse Transfer Capacitance			100	200	pF

• SWITCHING CHARACTERISTICS (T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Td(on)	Turn-on Delay Time	V_{DD}=180V,I_D=8.0A V_{GS}=10V,R_{GEN}=4.7Ω R_{GS}=4.7Ω			35	ns
Tr	Rise Time				65	ns
Td(off)	Turn-off Delay Time				150	ns
Tf	Fall Time				75	ns